

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
700V	0.6Ω @ V <sub>GS</sub> = 10V	11A

## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

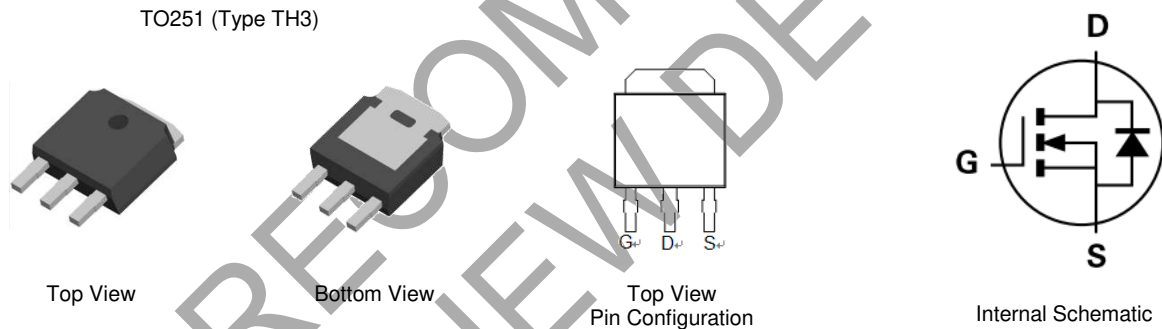
- Motor controls
- Backlighting
- AC-DC converters

## Features and Benefits

- Low On-Resistance
- High BV<sub>DSS</sub> Rating for Power Application
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

## Mechanical Data

- Package: TO251
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **(e3)**
- Weight: 0.33 grams (Approximate)

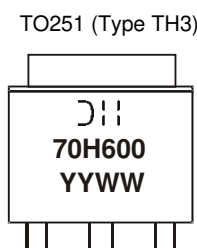


## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMJ70H600SH3	TO251 (Type TH3)	75 Pieces	Tube

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



= Manufacturer's Marking  
 70H600 = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Last Two Digits of Year (ex: 22 = 2022)  
 WW or WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	700	V
Gate-Source Voltage	V <sub>GSS</sub>	±30	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	I <sub>D</sub>	11 7	A
		T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	
Maximum Body Diode Forward Current (Note 6)	I <sub>S</sub>	1.8	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	11	A
Avalanche Current (Note 7)	I <sub>AS</sub>	1.5	A
		L = 60mH	
Avalanche Energy (Note 7)	E <sub>AS</sub>	67.5	mJ
		L = 60mH	
Peak Diode Recovery dv/dt (Note 7)	dv/dt	5	V/ns

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	113 45	W
		T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	57	°C/W
Thermal Resistance, Junction to Case (Note 5)	R <sub>θJC</sub>	1.1	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	700	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 700V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	100	nA	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	2.9	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.5	0.6	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.4A
Diode Forward Voltage	V <sub>SD</sub>	—	0.9	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 4.6A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	643	—	pF	V <sub>DS</sub> = 25V, f = 1MHz, V <sub>GS</sub> = 0V
Output Capacitance	C <sub>oss</sub>	—	524	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	13.5	—		
Gate Resistance	R <sub>g</sub>	—	3.6	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	18.2	—	nC	V <sub>DD</sub> = 380V, I <sub>D</sub> = 4.6A, V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>gs</sub>	—	2.5	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	8.5	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	11	—	ns	V <sub>DD</sub> = 380V, V <sub>GS</sub> = 10V, R <sub>g</sub> = 25Ω, I <sub>D</sub> = 4.6A
Turn-On Rise Time	t <sub>r</sub>	—	22	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	85	—		
Turn-Off Fall Time	t <sub>f</sub>	—	23	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	193	—	ns	I <sub>S</sub> = 4A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	1.6	—	µC	

- Notes:
5. Device mounted on infinite heatsink.
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  7. Guaranteed by design. Not subject to production testing.
  8. Short duration pulse test used to minimize self-heating effect.

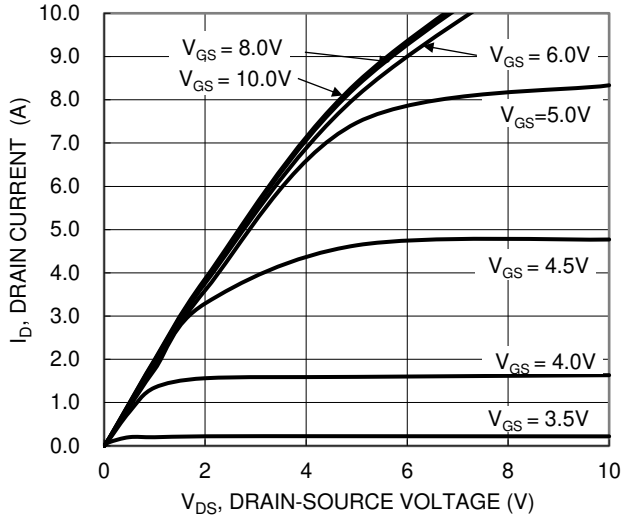


Figure 1. Typical Output Characteristic

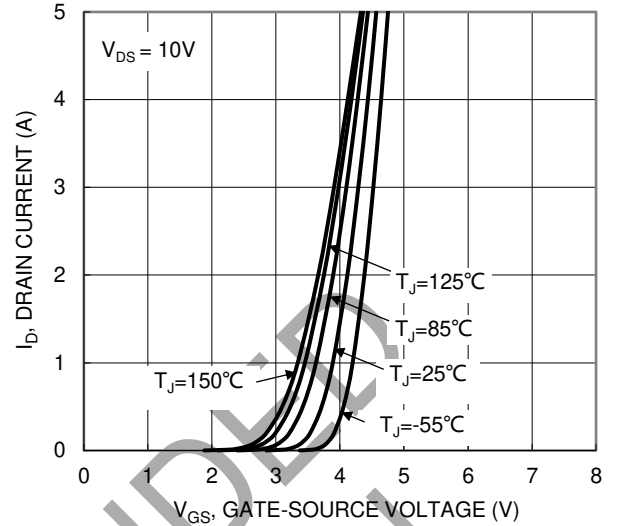


Figure 2. Typical Transfer Characteristic

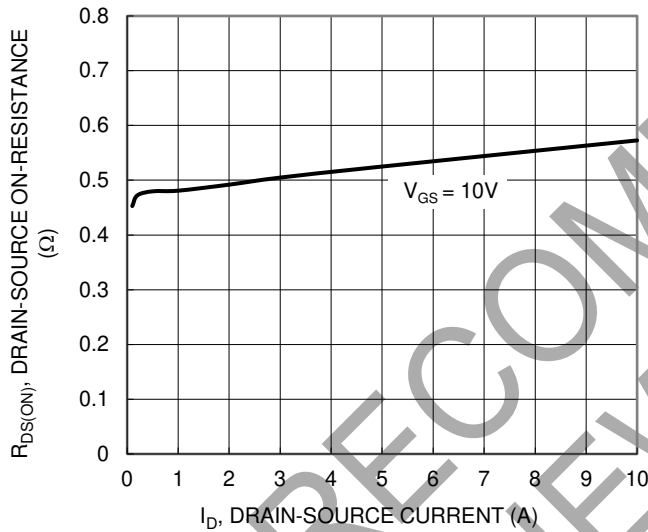


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

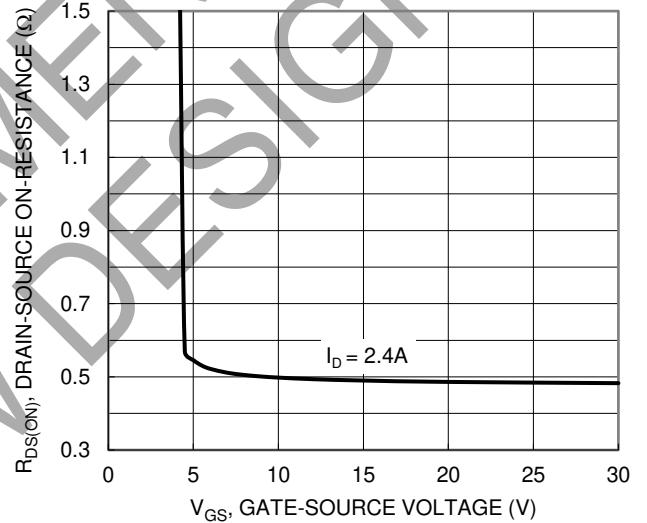


Figure 4. Typical Transfer Characteristic

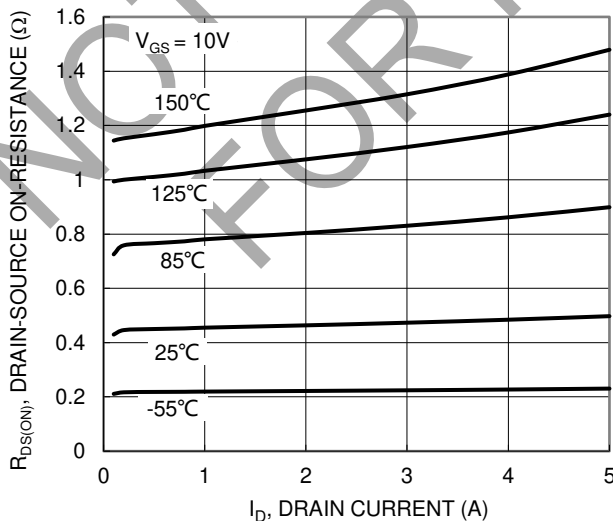


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

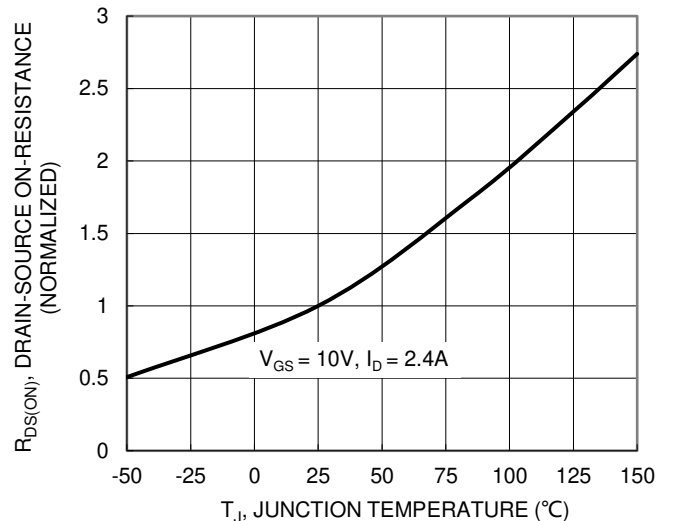


Figure 6. On-Resistance Variation with Temperature

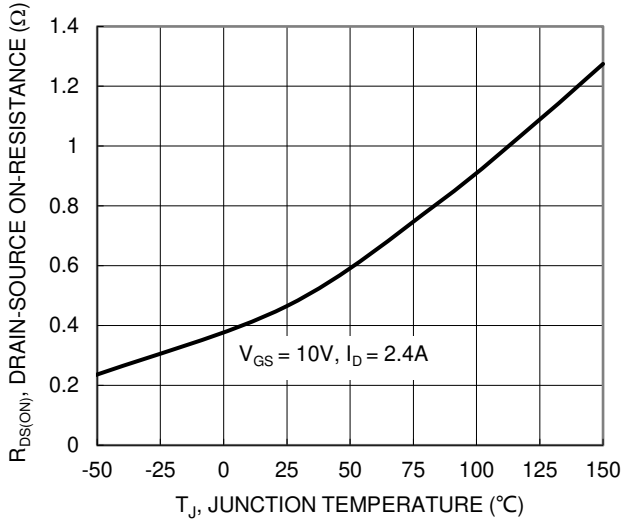


Figure 7. On-Resistance Variation with Temperature

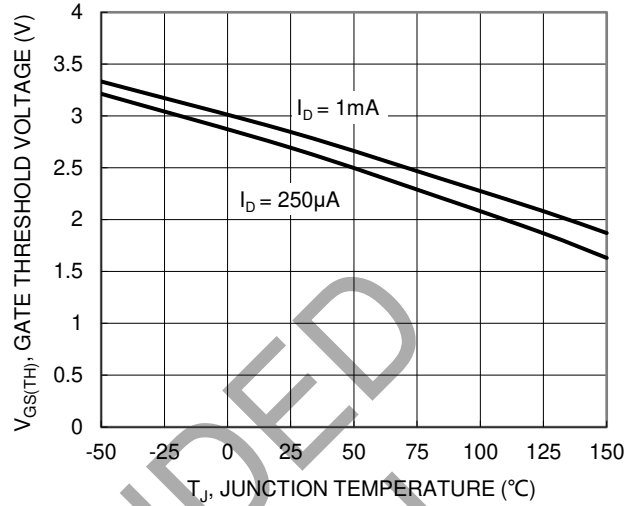


Figure 8. Gate Threshold Variation vs. Junction Temperature

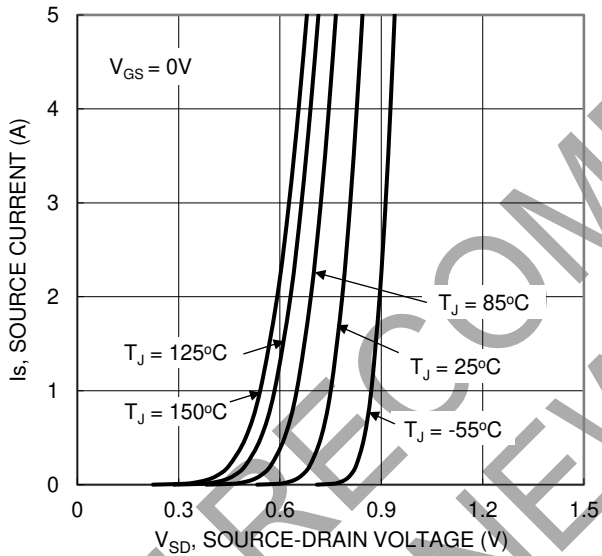


Figure 9. Diode Forward Voltage vs. Current

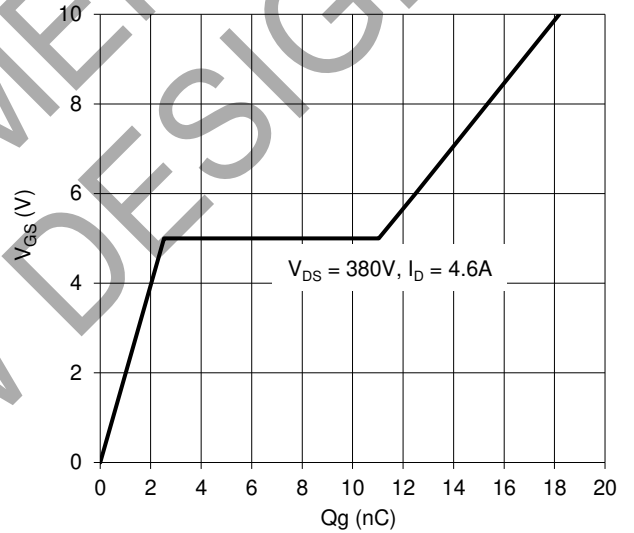


Figure 10. Gate Charge

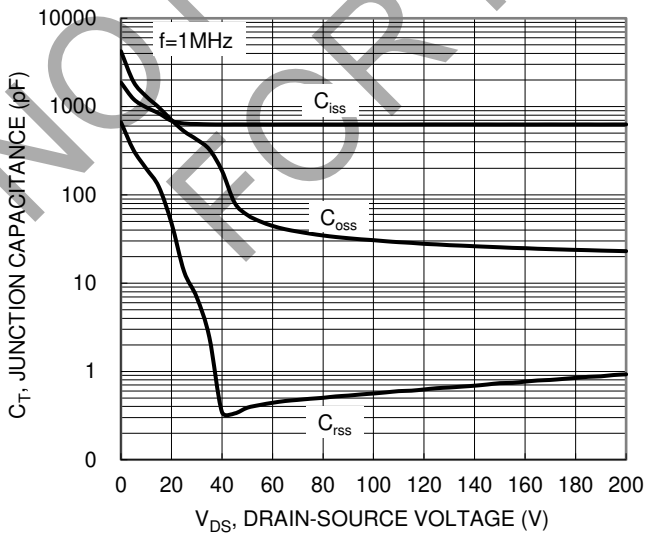


Figure 11. Typical Junction Capacitance

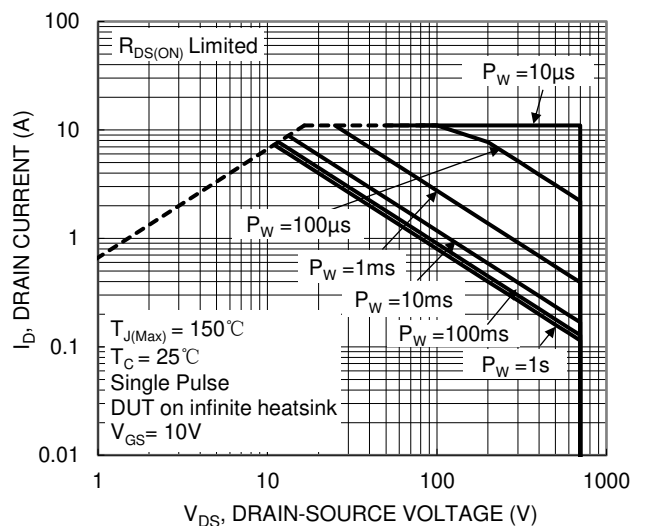


Figure 12. SOA, Safe Operation Area

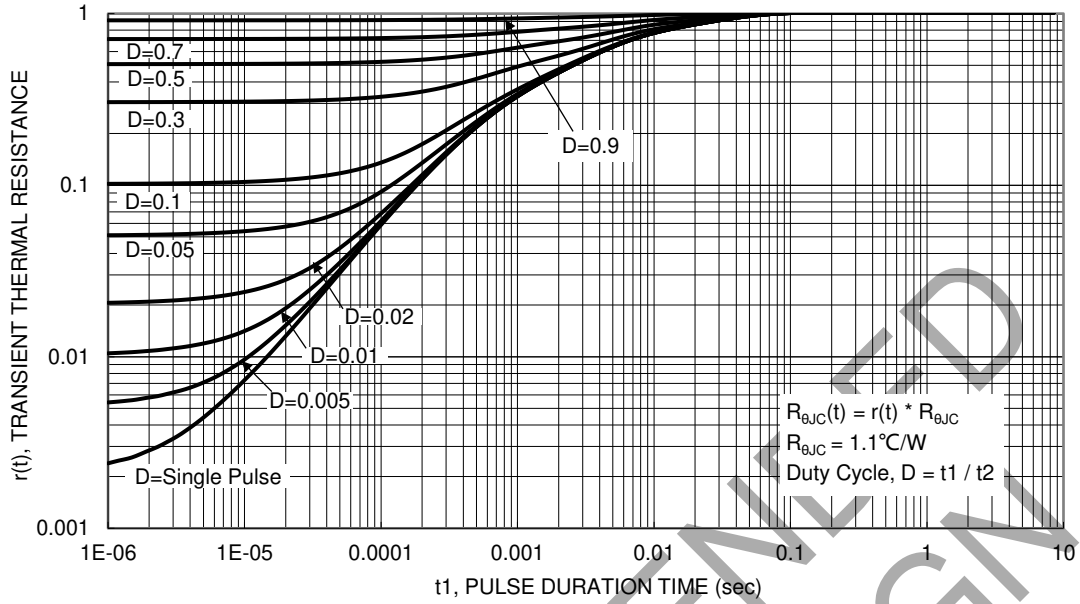


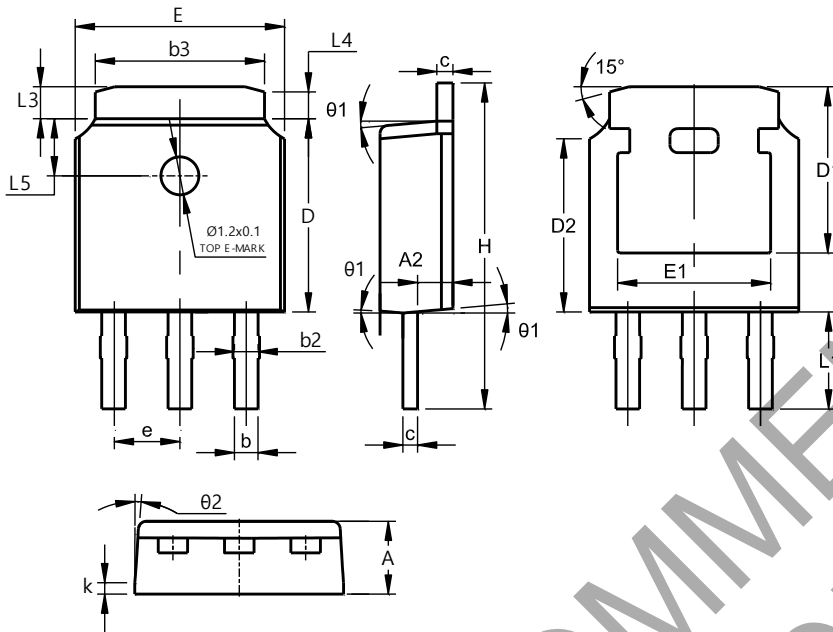
Figure 13. Transient Thermal Resistance

NOT RECOMMENDED FOR NEW DESIGN

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TO251 (Type TH3)**



TO251 (Type TH3)			
Dim	Min	Max	Typ
A	2.20	2.40	2.30
A2	0.97	1.17	1.07
b	0.68	0.90	0.78
b2	0.76	0.95	0.84
b3	5.20	5.50	5.33
c	0.43	0.63	0.53
D	5.98	6.22	6.10
D1	5.30 REF		
D2	5.26	5.66	5.46
e	2.286 BSC		
E	6.40	6.80	6.60
E1	4.63	5.03	4.83
H	9.40	9.85	9.62
k	0.40 REF		
L1	2.30	2.70	2.50
L3	0.88	1.28	1.02
L4	0.75 REF		
L5	1.65	1.95	1.80
theta1	5°	9°	7°
theta2	5°	9°	7°
All Dimensions in mm			

NOT RECOMMENDED FOR NEW DESIGN

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